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**High-performance flexible thermoelectrics via nanobinder-assisted screen printing**

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# High-performance flexible thermoelectrics via nanobinder-assisted screen printing

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## Abstract

Flexible thermoelectric devices (F-TEDs) have garnered significant attention for their potential applications in wearable electronics, by leveraging the human-environment temperature gradient for power generation and utilizing tiny electrical signal for cooling. Traditional thermoelectric film fabrication processes are hindered by limited scalability and insufficient mechanical stability, primarily due to energy-intensive and complex procedures. In this highlight, we review an innovative nanobinder-assisted screen printing method developed by Chen *et al.*, which integrates solvothermal synthesis and scalable fabrication to produce high-performance flexible thermoelectric films. This strategy employs Te nanorods as "nanobinders" to enhance flexibility and mechanical durability of Bi<sub>2</sub>Te<sub>3</sub> nanoplates. The films produced exhibit an impressive figure of merit (*ZT*) of about 1.3 at 303 K and retain excellent mechanical stability through 1,000 bending cycles. Moreover, the assembled F-TEDs demonstrate 1.2 mW cm<sup>-2</sup> power density with a cooling temperature variation of 11.7 K, underscoring their applicability in advanced wearable power systems and integrated circuit cooling. This scalable, cost-effective approach establishes a robust platform for flexible thermoelectrics and presents a pathway for exploring new material combinations.

## Keywords

Flexible thermoelectrics, Bi<sub>2</sub>Te<sub>3</sub>, Nanobinder-assisted fabrication, Screen printing, Wearable electronics

## Main text

As wearable electronic devices become increasingly ubiquitous, the demand for reliable and sustainable charging and cooling solutions continues to grow rapidly.<sup>[1]</sup> F-TEDs, or flexible thermoelectric devices, are gaining attention due to their potential to harness the temperature gradient between the external environment and human body for electricity generation or to enable cooling through targeted electrical power input.<sup>[2-4]</sup> This underscores the need for thermoelectric materials that combine high performance, flexibility, and stability under ambient conditions.<sup>[5]</sup>

Inorganic materials, particularly bismuth telluride (Bi<sub>2</sub>Te<sub>3</sub>), are renowned for their exceptional thermoelectric properties at room temperature, establishing them as prime

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3 candidates for F-TEDs.<sup>[6]</sup> Despite a remarkable dimensionless figure of merit ( $ZT$ ) of 1.2  
4 achieved through (00 $l$ )-oriented  $\text{Bi}_2\text{Te}_3$  films, the fabrication processes remain  
5 energy-intensive and complex, limiting their scalability. While screen printing provides a  
6 cost-effective and scalable approach, challenges persist in improving the densification and  
7 flexibility of films.<sup>[7]</sup> Furthermore, optimizing  $\text{Bi}_2\text{Te}_3$ 's thermoelectric performance  
8 necessitates precise powder design—balancing particle size for (00 $l$ ) orientation with initial  
9 thermoelectric efficiency. However, larger particle sizes introduce risks of cracking,  
10 compromising flexibility and stability.<sup>[8]</sup> Thus, addressing these barriers is critical for  
11 advancing high-performance,  $\text{Bi}_2\text{Te}_3$ -based flexible films, given their immense application  
12 potential.

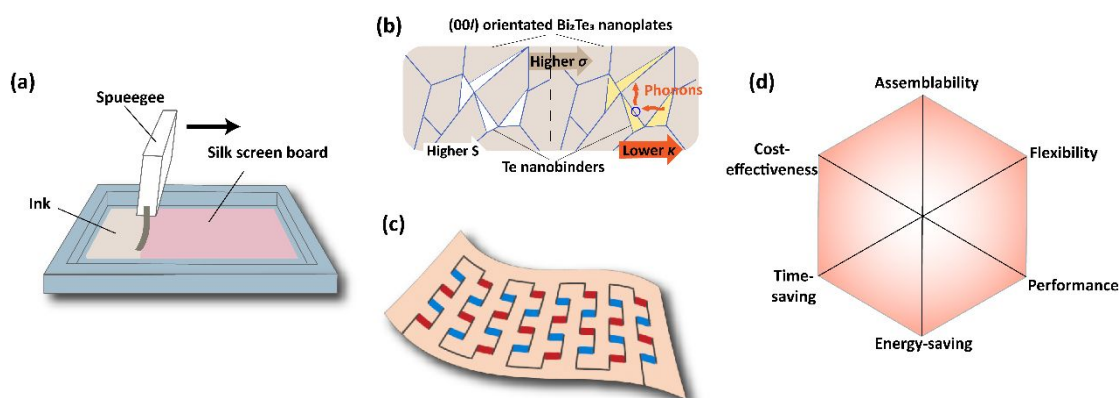
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16 A recent study by Chen *et al.*, published in *Science*, introduced an a pioneering and  
17 economical strategy that leverages solvothermal synthesis, together with screen printing  
18 to fabricate flexible thermoelectric films based on inorganic materials.<sup>[9]</sup> The films,  
19 composed of highly oriented  $\text{Bi}_2\text{Te}_3$  nanoplates and reinforced with Te nanorods that act  
20 as "nanobinders", demonstrate superior thermoelectric performance, exceptional  
21 flexibility, cost-effectiveness, and scalability.

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24 To fabricate flexible thermoelectric films, Chen *et al.* synthesized high-performance  
25 Ag-doped  $\text{Bi}_2\text{Te}_3$  nanoplates via solvothermal synthesis and mixed them with Te  
26 nanorods to create ink suitable for screen printing, as schematically shown in **Figure 1a**.  
27 The  $\text{Bi}_2\text{Te}_3$  nanoplates provide high (00 $l$ ) orientation and superior thermoelectric  
28 performance, while the Te nanorods serve as "nanobinders", enhancing film density and  
29 flexibility. In particular, the introduction of Te plays crucial roles in decoupling the  
30 electrical and thermal transports for further optimizing the thermoelectric performance of  
31  $\text{Bi}_2\text{Te}_3$  (**Figure 1b**). Firstly, the incorporation of Te nanorods establishes energy-filtering  
32 barriers that increase the Seebeck coefficient ( $S$ ) while retaining very high levels of  
33 electrical conductivity ( $\sigma$ ), leading to an impressive power factor ( $PF = S^2\sigma$ ) of  $18.5 \mu\text{W}$   
34  $\text{cm}^{-1} \text{K}^{-2}$ . Secondly, Te addition in  $\text{Bi}_2\text{Te}_3$  introduces lattice defects that strengthen phonon  
35 scattering greatly, thereby causing a reduction in lattice thermal conductivity ( $\kappa_l$ ) to about  
36  $0.19 \text{ W m}^{-1} \text{K}^{-1}$ . This modification results in a  $ZT$  of approximately 1.3 at 303 K,  
37 establishing the material as a leading candidate in the field of flexible thermoelectrics.  
38 Furthermore, mechanical tests show that the films exhibit only a 2% performance loss  
39 after enduring 1,000 bending cycles, highlighting their exceptional flexibility and  
40 durability.

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46 More importantly, Chen *et al.* designed the high-performance p-type and n-type  
47 flexible thermoelectric films obtained in the previous step into F-TED, as depicted  
48 schematically in **Figure 1c**. Under a temperature gradient of 20 K, the output power  
49 density of the assembled F-TED reaches as high as  $1.2 \text{ mW cm}^{-2}$ , with the corresponding  
50 normalized power density exceeding  $3 \mu\text{W cm}^{-2} \text{K}^{-2}$ , significantly outperforming other  
51 printing-based inorganic thermoelectric devices. On the other hand, the F-TED  
52 demonstrates a cooling temperature difference of 11.7 K when the input current is 84 mA,  
53 demonstrating its promising application potential for cooling advanced integrated circuit  
54 (IC) devices.

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58 In conclusion, the nanobinder-assisted screen printing method offers significant  
59 advantages in terms of thermoelectric performance, flexibility, scalability, and cost- and  
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time-efficiency, thereby making it a compelling approach for wearable power generation and cooling applications. The resulting films, composed of highly oriented  $\text{Bi}_2\text{Te}_3$  nanoplates reinforced with Te nanorods functioning as "nanobinders", exhibit superior thermoelectric performance and exceptional mechanical flexibility. These attributes not only highlight their potential as a promising "hexagonal warrior" (**Figure 1d**) in the field of flexible thermoelectrics but also demonstrate its potential for large-scale production of flexible thermoelectric materials, including other inorganic film systems. Developing suitable nanobinders for other high-performance thermoelectric systems, such as SnSe-based materials,<sup>[10]</sup> could further pave the way for achieving even higher thermoelectric performance in the future.



**Figure 1.** (a) Schematic diagram illustrating the screen-printing process. (b) Structural illustration of screen-printed  $\text{Bi}_2\text{Te}_3$  thin films, highlighting their (00 $l$ )-oriented alignment and morphology (c) **Structure of screen-printed flexible thermoelectric device.** (d) Conceptual schematic depicting the constructed flexible thermoelectrics as analogous to a "hexagonal warrior".

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### Conflict of interest

The authors declare no conflict of interest.

### Author contributions

This highlight was drafted by Dr. Chengchao Hu and revised by Dr. Bingchao Qin and Prof. Li-Dong Zhao. All authors have approved the final version of the manuscript.

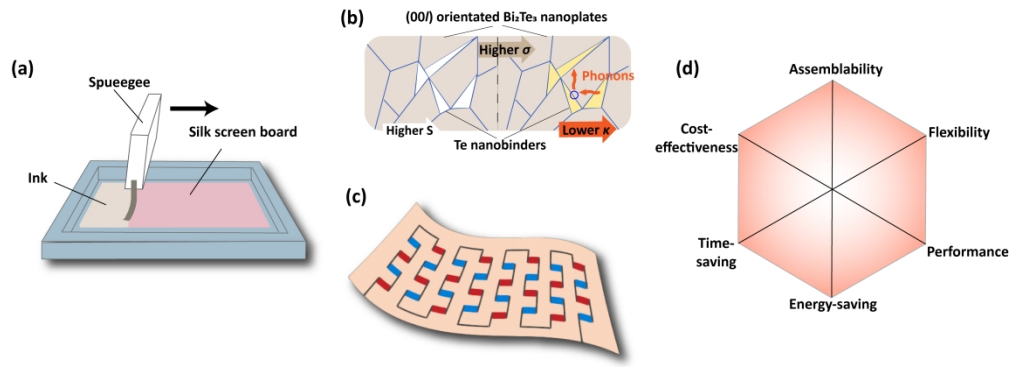
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